

Silicon PNP Power Transistors

BD136 BD138 BD140

DESCRIPTION

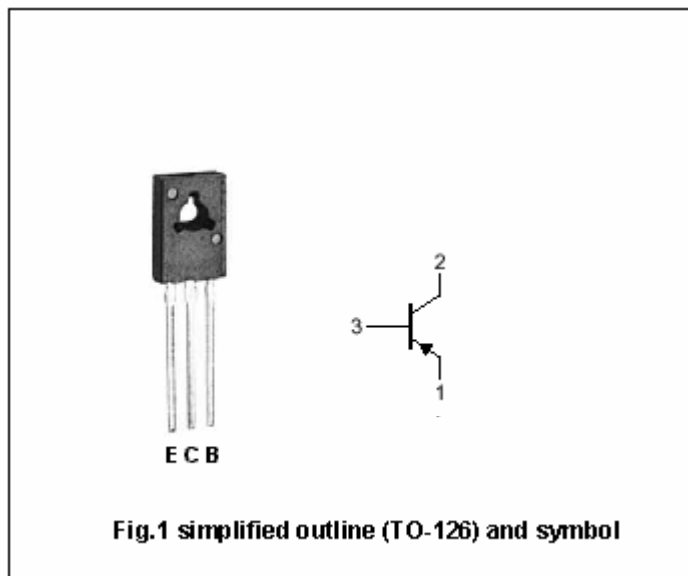
- With TO-126 package
- High current
- Complement to type BD135/137/139

APPLICATIONS

- Driver stages in high-fidelity amplifiers and television circuits

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	BD136	Open emitter	-45	V
		BD138		-60	
		BD140		-100	
V_{CEO}	Collector-emitter voltage	BD136	Open base	-45	V
		BD138		-60	
		BD140		-100	
V_{EBO}	Emitter -base voltage		Open collector	-5	V
I_C	Collector current (DC)			-1.5	A
I_{CM}	Collector current-Peak			-2	A
I_{BM}	Base current-Peak			-1	A
P_t	Total power dissipation		$T_{mb} \leq 70^\circ\text{C}$	8	W
T_j	Junction temperature			150	℃
T_{stg}	Storage temperature			-65~150	℃
T_{amb}	Operating ambient temperature			-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-a}$	Thermal resistance from junction to ambient	100	K/W
$R_{th\ j-mb}$	Thermal resistance from junction to mounting base	10	K/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =-0.5A; I _B =-50mA			-0.5	V
V _{BE}	Base-emitter voltage	I _C =-500mA; V _{CE} =-2V			-1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-30V; I _E =0			-100	nA
		V _{CB} =-30V; I _E =0 T _j =125°C			-10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-100	nA
h _{FE-1}	DC current gain	I _C =-5mA; V _{CE} =-2V	40			
h _{FE-2}	DC current gain BD136-10;BD138-10;BD140-10 BD136-16;BD138-16;BD140-16	I _C =-150mA; V _{CE} =-2V	63 63 100		250 160 250	
h _{FE-3}	DC current gain	I _C =-500mA; V _{CE} =-2V	25			
f _T	Transition frequency	I _C =-50mA; V _{CE} =-5V; f=100MHz		160		MHz

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PACKAGE OUTLINE

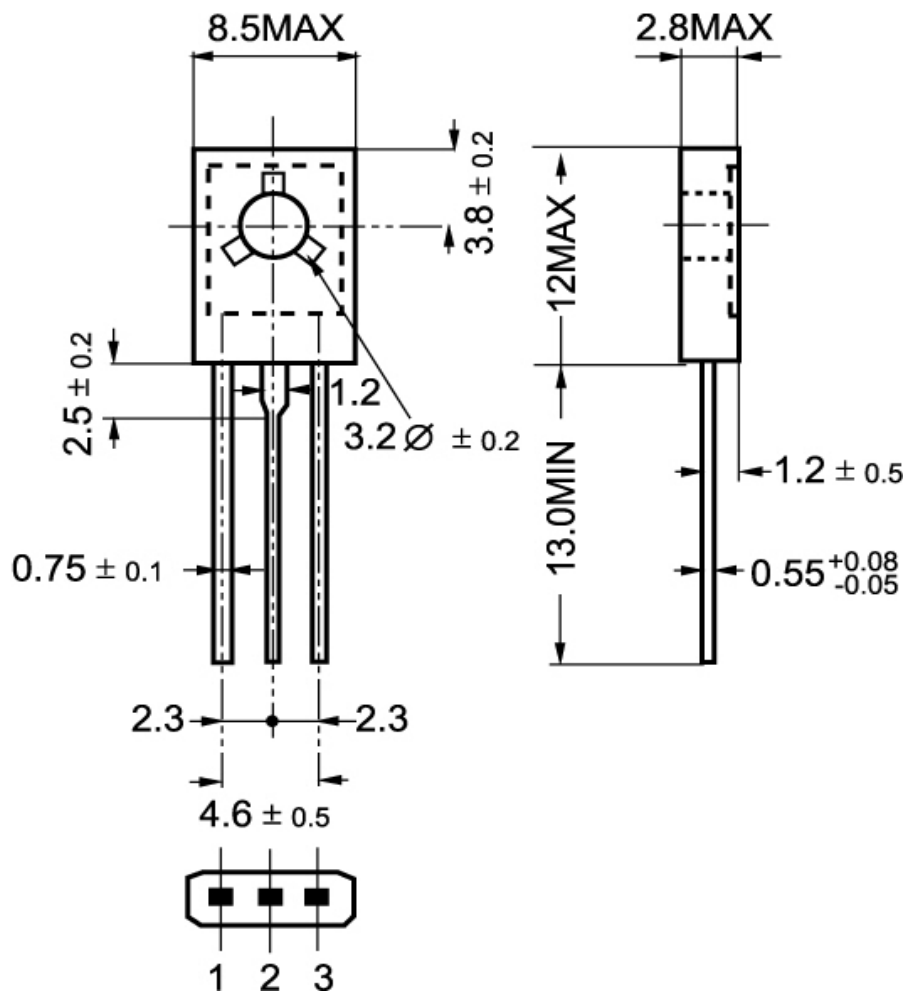


Fig.2 Outline dimensions